



Shenzhen Tuofeng Semiconductor Technology Co., Ltd

N - CHANNEL ENHANCEMENT MODE POWER MOSFET

SGT MOS、低内阻、低结电容开关损耗小

TF040N03NG**• General Description**

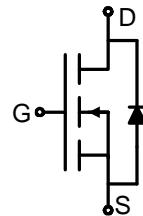
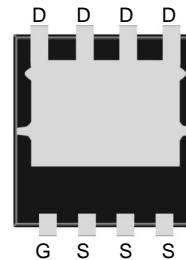
The TF040N03NG uses advanced trench technology and design to provide excellent RDS(ON) withlowgate charge. It can be used in a wide variety of applications.

• Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Power Tools

• Product Summary $V_{DS} = 30V \quad I_D = 70A$ $R_{DS(10V\ TYP)} = 4.1m\Omega$ $R_{DS(4.5V\ TYP)} = 5.8m\Omega$ **PDFNWB5x6-8L****• Package Marking and Ordering Information:**

Part NO.	TF040N03NG
Marking1	040N03NG:TF040N03NG
Marking2	TF:tuofeng; Y:year code; X:Week; AA:device code;
Basic ordering unit (pcs)	5000

• Absolute Maximum Ratings (T_C =25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	70	A
	$I_D @ T_C = 75^\circ C$	49	A
	$I_D @ T_C = 100^\circ C$	42	A
Pulsed Drain Current ①	I_{DM}	245	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	45	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C
Single Pulse Avalanche Energy	E_{AS}	55	mJ



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Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	3.5	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	45	° C/W
Soldering temperature, wavesoldering for 8 s	T _{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	30	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA	1.1	1.5	2.1	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30 V _{GS} = 0V	-	-	1.0	μA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} = 0V	-	-	±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	4.1	5.0	mΩ
		V _{GS} =4.5V, I _D =15A	-	5.8	7.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 25V, I _D =15A	-	15	-	S
Source-drain voltage	V _{SD}	I _S =15A	-	0.80	1.20	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz V _{DS} =15V V _{GS} = 0V	-	750	-	pF
Output capacitance	C _{oss}		-	333	-	
Reverse transfer capacitance	C _{rss}		-	32.0	-	

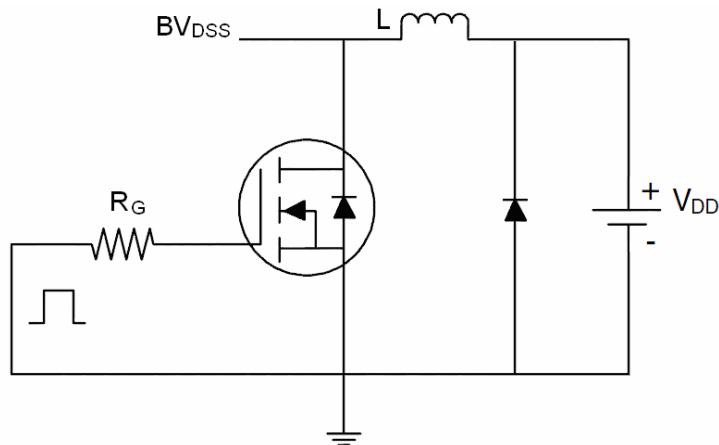
•Switching Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Turn-on delay time	t _{d(on)}	V _{DD} = 15V I _D = 15A R _G = 3.0 V _{GS} = 10V	-	4.4	-	nS
Rise time	t _r		-	23.6	-	
Turn-off delay time	t _{d(off)}		-	13.0	-	
Fall time	t _f		-	6.2	-	

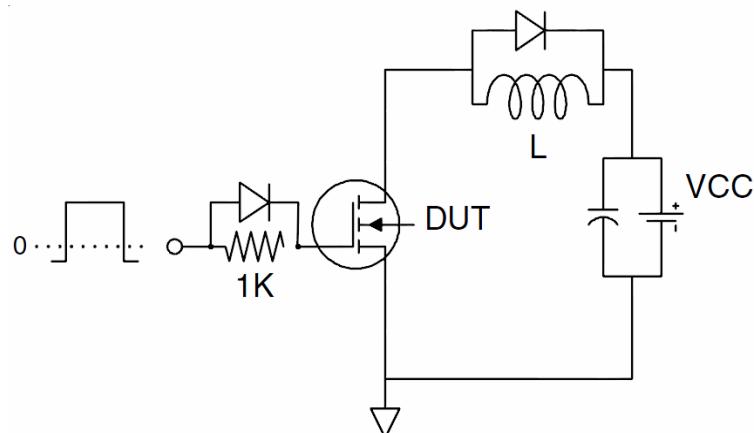
Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Test Circuit

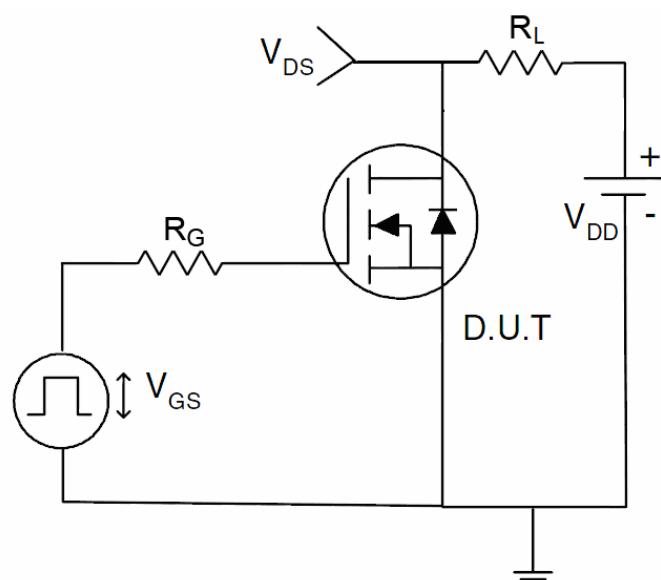
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

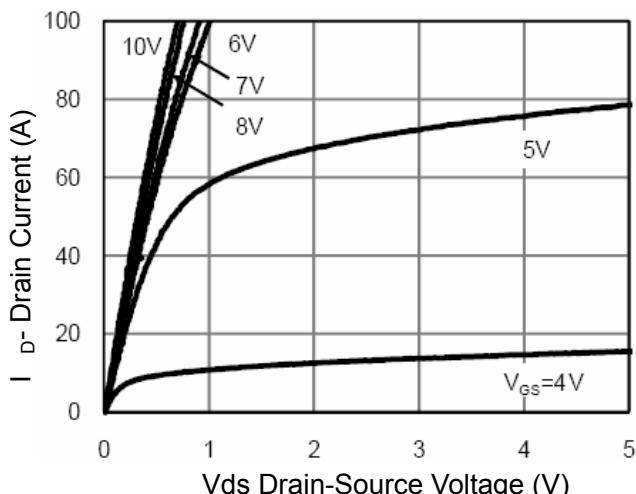


Figure 1 Output Characteristics

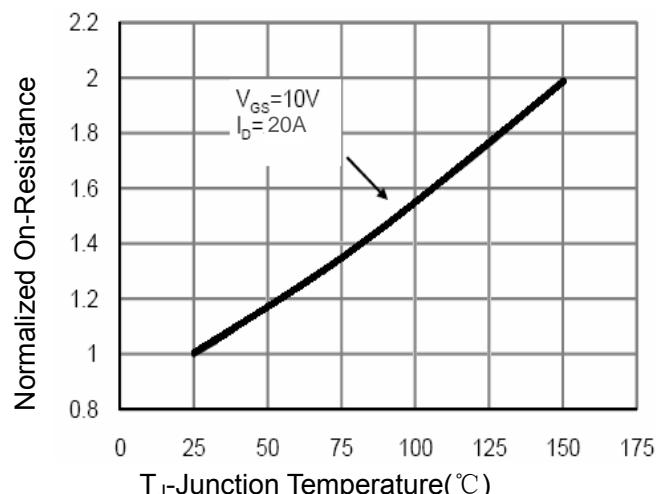


Figure 4 Rdson-JunctionTemperature

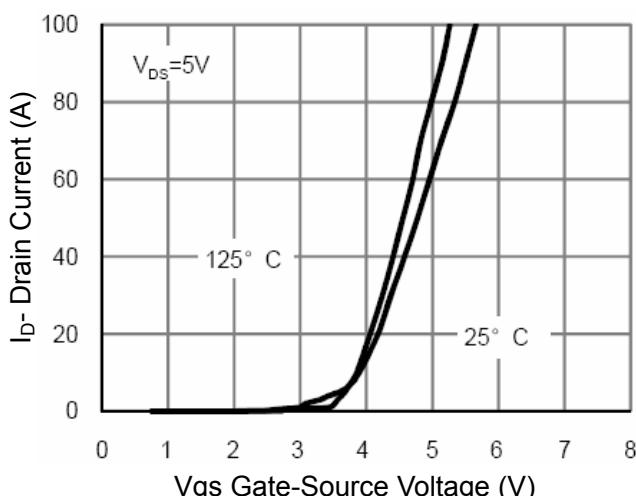


Figure 2 Transfer Characteristics

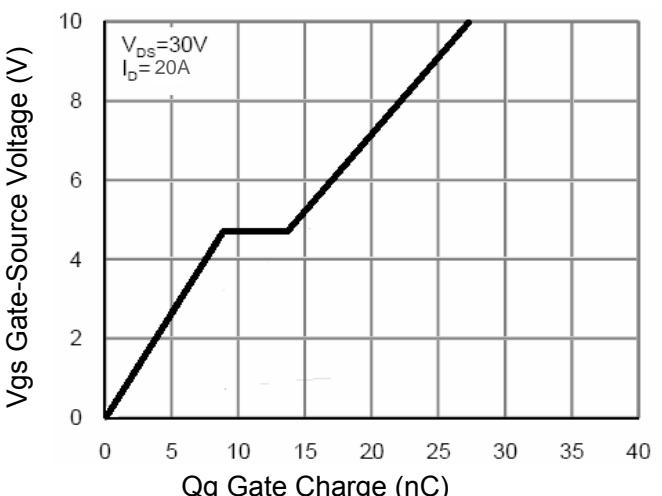


Figure 5 Gate Charge

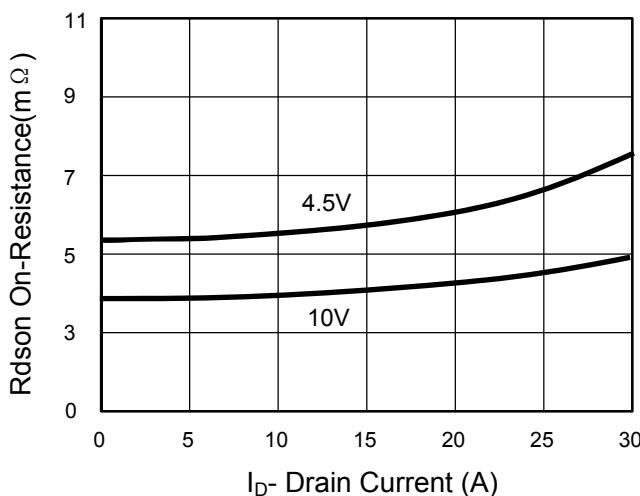


Figure 3 Rdson- Drain Current

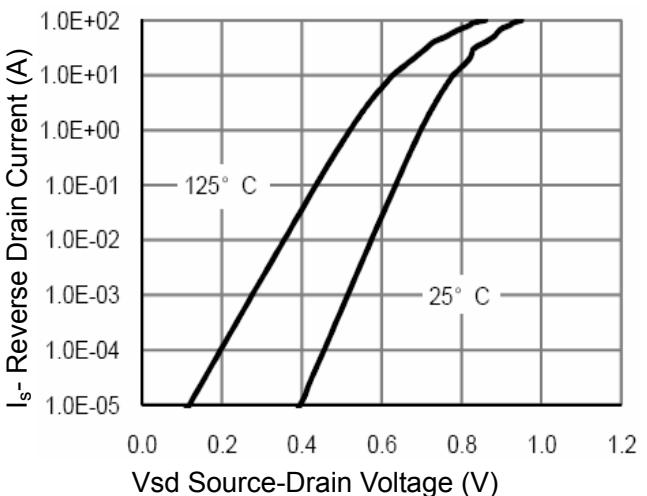


Figure 6 Source- Drain Diode Forward

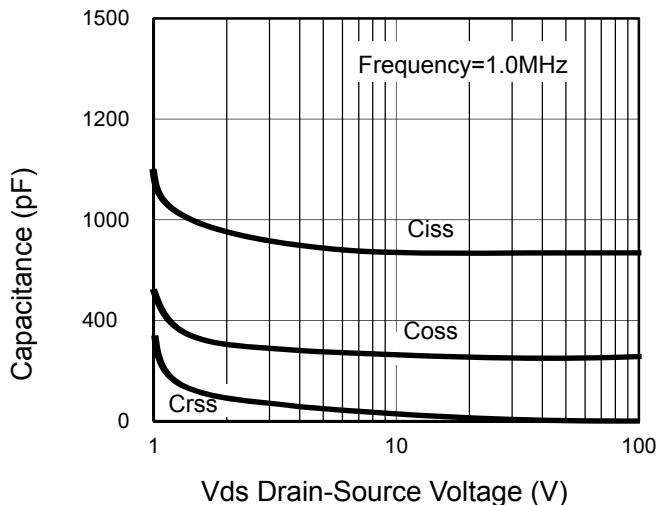


Figure 7 Capacitance vs Vds

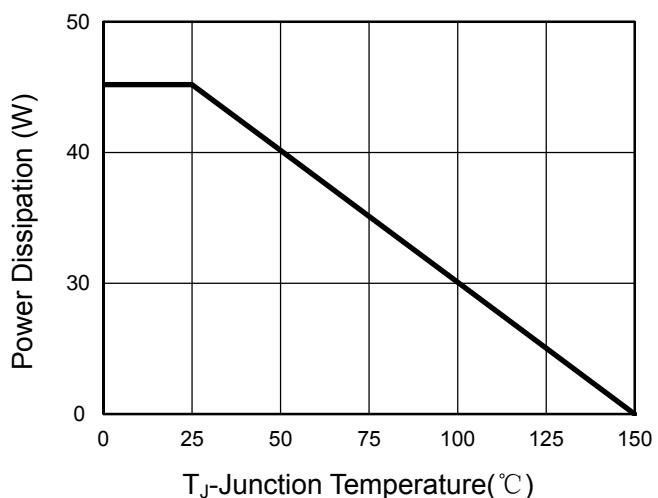


Figure 9 Power De-rating

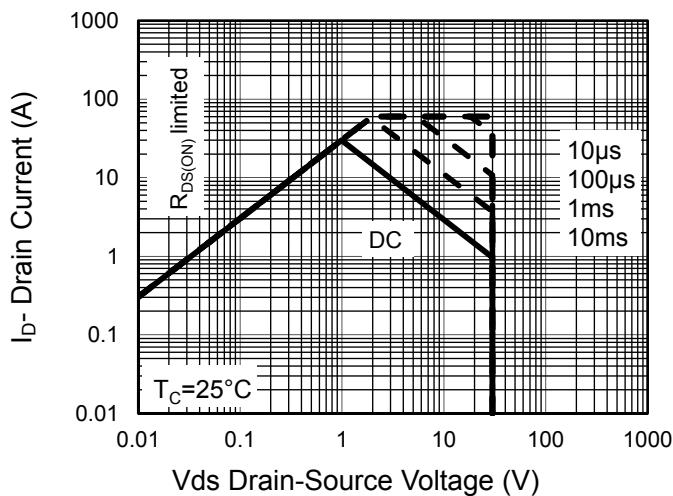


Figure 8 Safe Operation Area

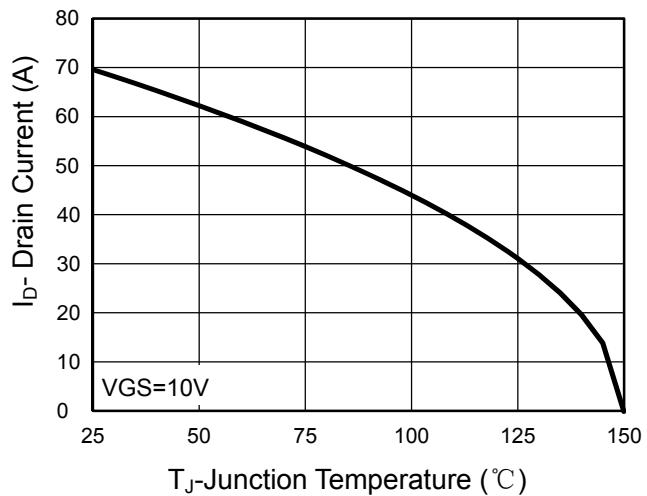


Figure 10 Current De-rating

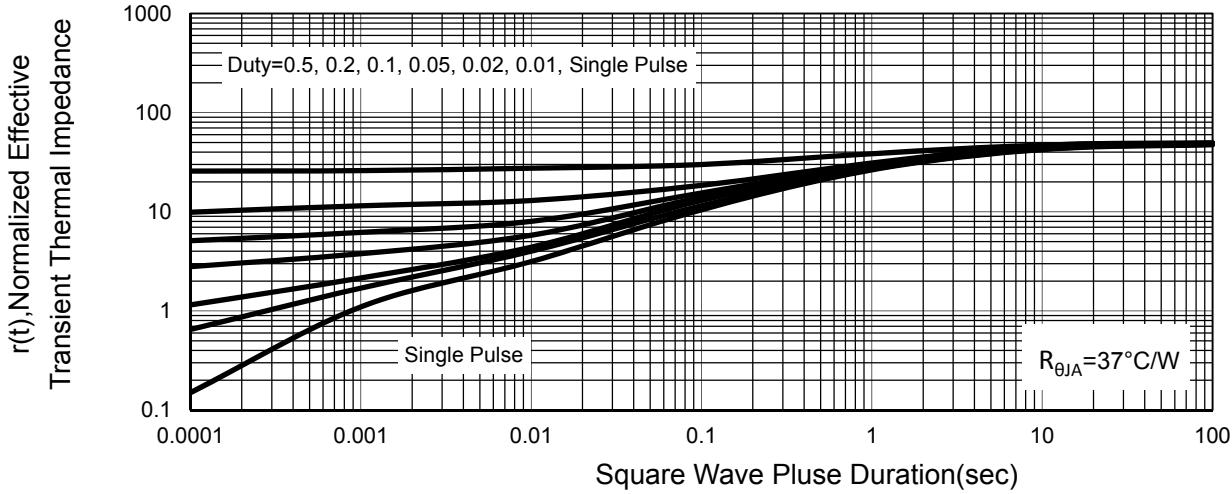
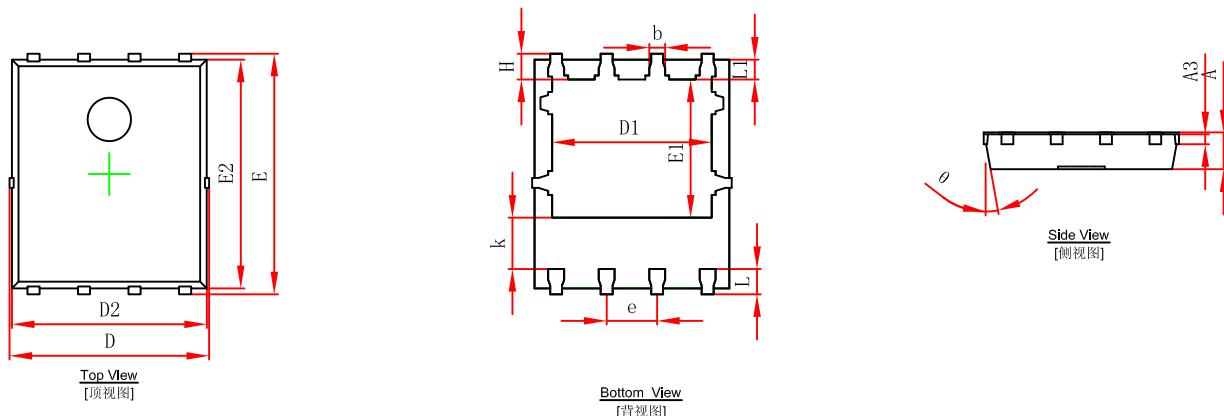


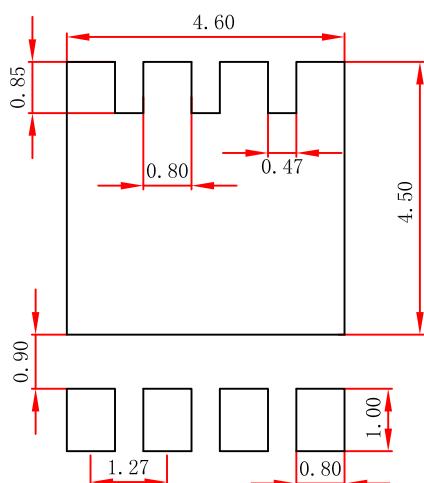
Figure 11 Normalized Maximum Transient Thermal Impedance



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N - CHANNEL ENHANCEMENT MODE POWER MOSFET**SGT MOS、低内阻、低结电容开关损耗小****TF040N03NG****PDFNWB5x6-8L Package Outline Dimensions**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFNWB5x6-8L Suggested Pad Layout**Note:**

1. Controlling dimension:in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.